

Title (en)

TURN-OFF POWER SEMICONDUCTOR COMPONENT

Title (de)

ABSCHALTbares LEISTUNGSHALBLEITERBAUELEMENT

Title (fr)

COMPOSANT DE PUISSANCE A SEMI-CONDUCTEUR INTERRUPTIBLE

Publication

EP 0742958 A1 19961120 (DE)

Application

EP 95908217 A 19950130

Priority

- DE 4402884 A 19940201
- EP 9500307 W 19950130

Abstract (en)

[origin: DE4402884C1] The semiconductor element has a number of adjacent cells formed in the body of the semiconductor, acting as a p-emitter zone (1), a n-base zone (2) and a p-base zone (3) in which a n-emitter zone (4) is embedded. At least one p-zone (5) is embedded in the n-emitter zone, providing a ballast resistance, provided with 2 ohmic contacts. One of the contacts acts as an outer cathode metallisation (K), which has no contact with the n-emitter zone, the other acting as a floating contact (K') in ohmic contact with the n-emitter zone.

IPC 1-7

H01L 29/745; H01L 29/749

IPC 8 full level

H01L 29/08 (2006.01); **H01L 29/74** (2006.01); **H01L 29/744** (2006.01); **H01L 29/749** (2006.01)

CPC (source: EP US)

H01L 29/0839 (2013.01 - EP US); **H01L 29/744** (2013.01 - EP US)

Citation (search report)

See references of WO 9521461A1

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

DE 4402884 C1 19950518; EP 0742958 A1 19961120; US 5731605 A 19980324; WO 9521461 A1 19950810

DOCDB simple family (application)

DE 4402884 A 19940201; EP 9500307 W 19950130; EP 95908217 A 19950130; US 68270296 A 19960726